

L9	6	("4414297").URPN.	USPAT	OR	ON	2006/01/13 10:52
L10	253	esd same output near protect\$3 and (MOS MOSFET FET field adj effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 12:02
L11	5	esd same output near protect\$3 and (MOS MOSFET FET field adj effect) same increase near resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 12:05
L12	8	esd same output near protect\$3 and (MOS MOSFET FET field adj effect) same increase near3 resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 12:07
L13	61	esd same output and (MOS MOSFET FET field adj effect) same increase near3 resistance	US>PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 12:07